



Features

- For general purpose applications
- Metal silicon schottky barrier device which is protected by a PN junction guard ring. The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications

Mechanical Data

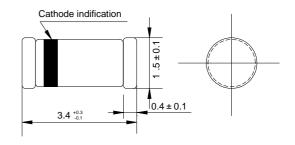
- ♦ Case:JEDEC MINI-MELF,glass case
- Polarity: Color band denotes cathode end
- Weight: Approx 0.031 grams

LL45

Small Signal Schottky Diodes

VOLTAGE RANGE: 15 V CURRENT: 30 mA

MINI-MELF



Dimensions in millimeters

ABSOLUTE RATINGS(LIMITING VALUES)

	Symbols	Value	UNITS
Peak reverse voltage	V_{RRM}	15	V
Forward continuous current	I _F	30	mA
Surge non repetitive forward current tp 1s	I _{FSM}	60	mA
Junction tenperature	T _J	125	$^{\circ}\!\mathbb{C}$
Storage temperature range	T _{STG}	-55+ 150	$^{\circ}\!\mathbb{C}$
1)Valid provided that electrodes are kept at ambient temperature.	•		•

ELECTRICAL CHARACTERISTICS

(Ratings at 25℃ ambient temperature unless otherwise specified)

	Symbols	Min.	Тур.	Max.	UNITS
Reverse breakdown voltage @ I _R =10 µ A	V_R	15			V
Leakage current @ V _R =6V	I _R			100	nA
Forw ard voltage drop @ I _F =1.0mA				0.38	
Test pulse:tp 300μ s, < 2% I _F =10mA	V_{F}			0.5	V
I _F =30mA				1.0	
Junction capacitance @ V _R =1.0V,f=1MHz	CJ			1.1	pF
Termal resistance junction to ambient air	$R_{ heta JA}$			400	K/W